

06-06-07

18W

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicants: KIM, Hyun-Jae and KANG, Myung-Koo
Assignee: SAMSUNG ELECTRONICS CO., LTD.
Title: METHOD OF POLYCRYSTALLIZATION, METHOD OF
MANUFACTURING POLYSILICON THIN FILM TRANSISTOR,
AND LASER IRRADIATION DEVICE THEREFOR
Application No.: 10/532,459 Filing Date: 11/02/2005
Examiner: BOOTH, Richard A. Group Art Unit: 2812
Docket No.: AB-1432 US Confirmation No.: 1783

San Jose, California
June 4, 2007

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

RESPONSE TO RESTRICTION REQUIREMENT

Dear Sir:

In response to the Office Action having a mailing date of May 4, 20007, Applicants hereby elect Group II (claims 2-7, drawn to a method of making a thin film transistor) for further prosecution. Applicants withdraw the non-elected claim of Group I (claim 1, drawn to a device for irradiating a laser beam), reserving the right to prosecute that claim in another application.

The Examiner is invited to call the undersigned at (408) 392-9250 with any questions regarding the above-identified application.

**EXPRESS MAIL LABEL NO.
EV 947 397 329 US**

Respectfully submitted,

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